

Silicon PNP Power Transistors

2SB988

DESCRIPTION

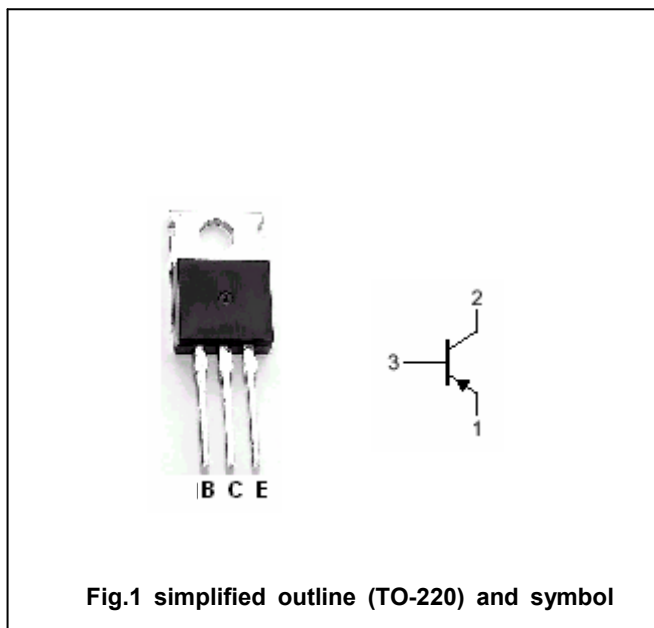
- With TO-220C package
- Low collector saturation voltage

APPLICATIONS

- For vertical output and general purpose applicaitons

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-60	V
V _{CEO}	Collector-emitter voltage	Open base	-60	V
V _{EBO}	Emitter-base voltage	Open collector	-7	V
I _C	Collector current (DC)		-3	A
I _B	Base current		-0.5	A
P _C	Collector dissipation	T _C =25°C	30	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-50~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-30mA; I _B =0	-60			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-3A; I _B =-0.3A			-1.0	V
V _{BE}	Base-emitter on voltage	I _C =-0.5A; V _{CE} =-5V			-1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-60V; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-7V; I _C =0			-0.1	mA
h _{FE-1}	DC current gain	I _C =-0.5A; V _{CE} =-5V	60		200	
h _{FE-2}	DC current gain	I _C =-3A; V _{CE} =-5V	20			
C _{OB}	Output capacitance	I _E =0; V _{CB} =-10V; f=1MHz		150		pF
f _T	Transition frequency	I _C =-0.5A; V _{CE} =-5V		9		MHz

◆ h_{FE-1} Classifications

O	Y
60-120	100-200

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PACKAGE OUTLINE



Fig.2 Outline dimensions (unindicated tolerance:±0.10mm)